

SANYO

No.3187

2SA1745/2SC4555

PNP/NPN Epitaxial Planar Silicon Transistor

Low-Frequency General-Purpose
Amp Applications**Features**

- Very small-sized package permitting the 2SA1745/2SC4555-applied sets to be made small and slim
- Low collector-to-emitter saturation voltage

(): 2SA1745

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V_{CBO}	(-)20	V
Collector to Emitter Voltage	V_{CEO}	(-)15	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)500	mA
Collector Current(Pulse)	I_{CP}	(-)1	A
Collector Dissipation	P_C	150	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	- 55 to + 150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)15V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)2V, I_C = (-)10mA$	135*		600*	
	$h_{FE}(2)$	$V_{CE} = (-)2V, I_C = (-)400mA$	(70)80			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)2V, I_C = (-)50mA$		300 (400)		MHz
Output Capacitance	c_{ob}	$V_{CB} = (-)10V, f = 1MHz$		(6.5)4.0		pF
C-E Saturation Voltage	$V_{CE(sat)}(1)$	$I_C = (-)5mA, I_B = (-)0.5mA$		(-)15	(- 35)30	mV
	$V_{CE(sat)}(2)$	$I_C = (-)200mA, I_B = (-)10mA$		160	300	mV
				(- 200)	(- 360)	
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)200mA, I_B = (-)10mA$		(-)0.95	(-)1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)20			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V

*: The 2SA1745/2SC4555 are classified by 10mA h_{FE} as follows:

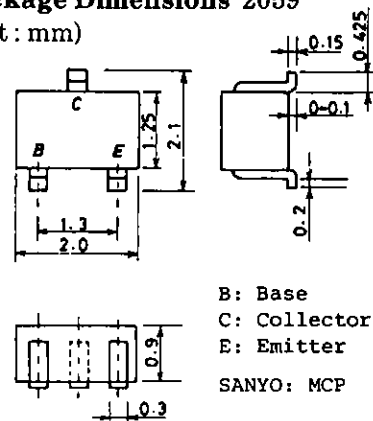
135 5 270	200 6 400	300 7 600
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Marking 2SA1745 : ES

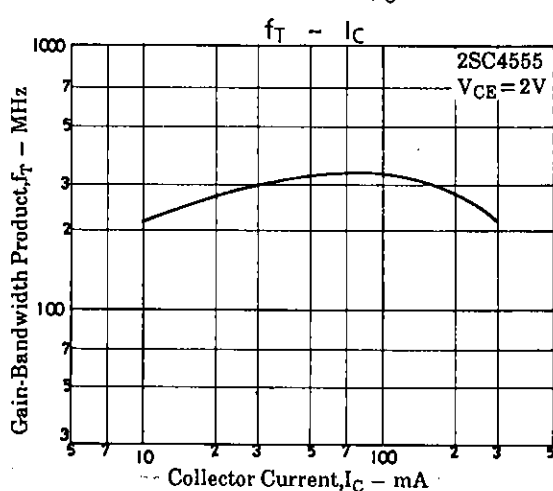
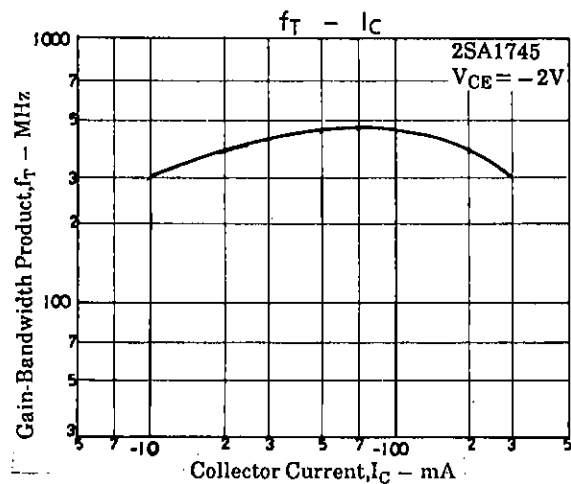
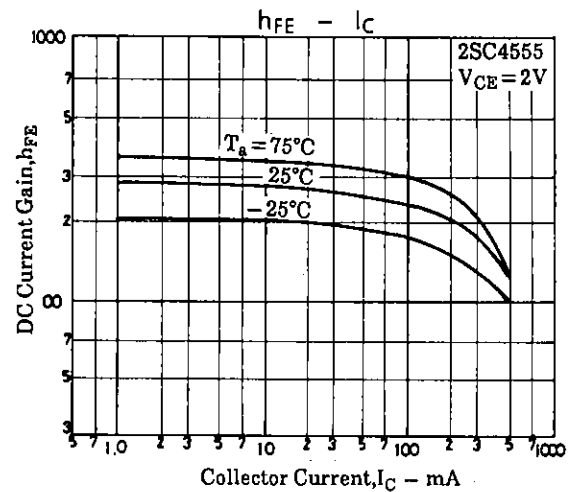
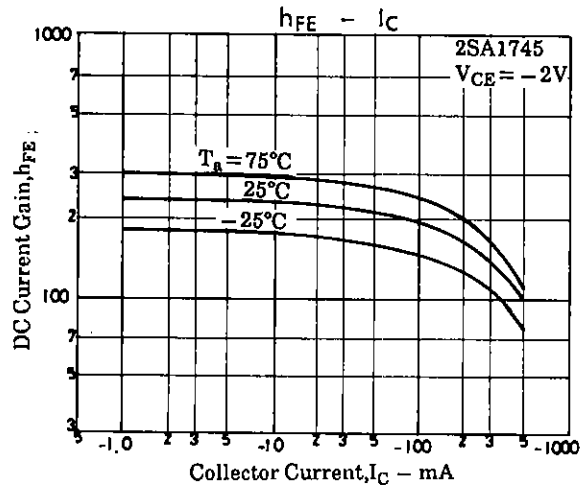
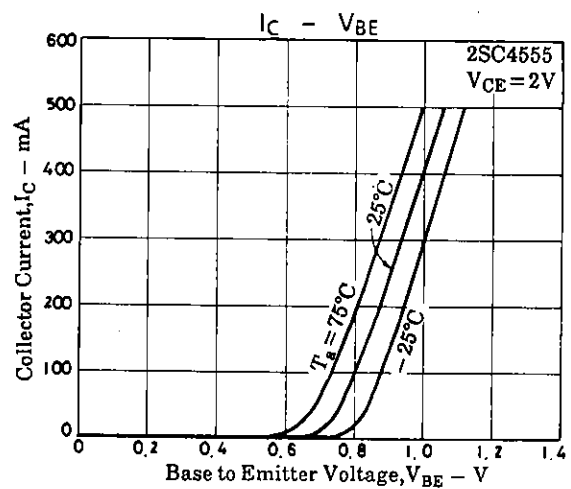
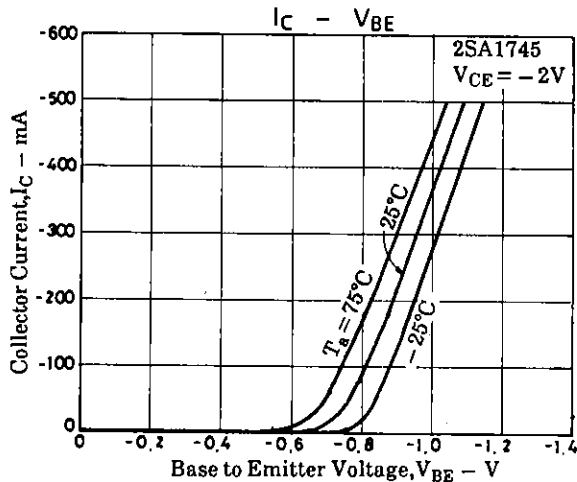
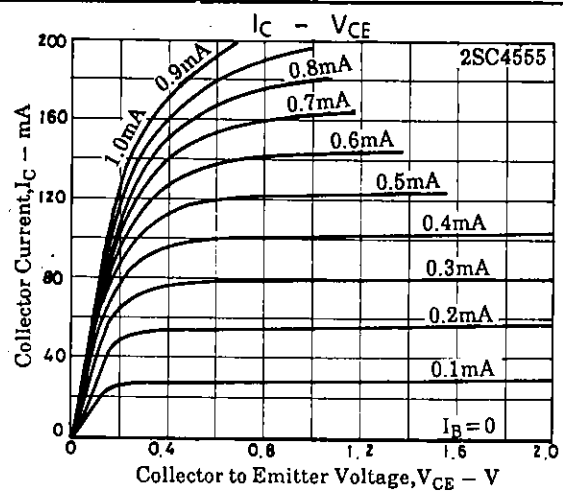
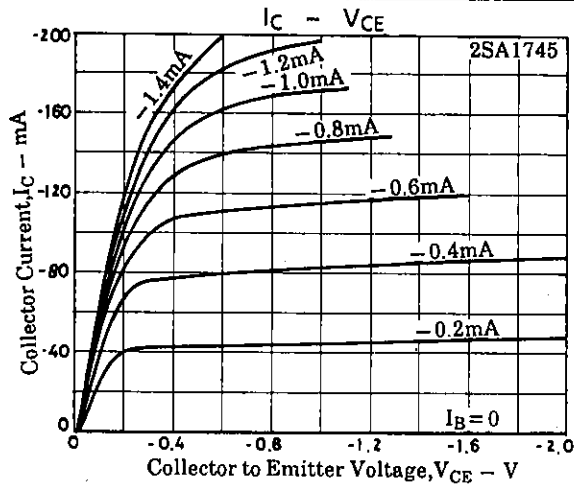
2SC4555 : UT

 h_{FE} rank : 5,6,7**Package Dimensions 2059**

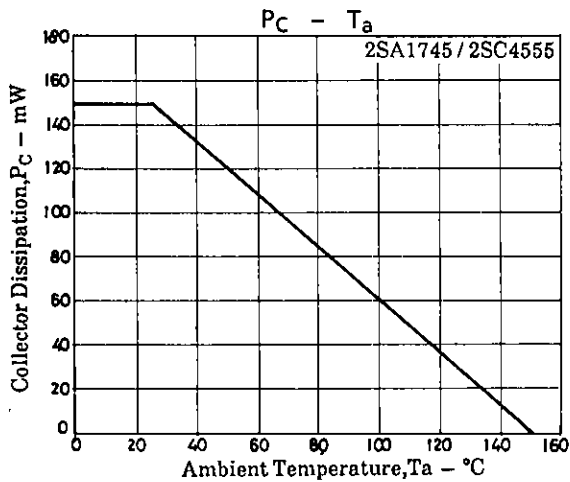
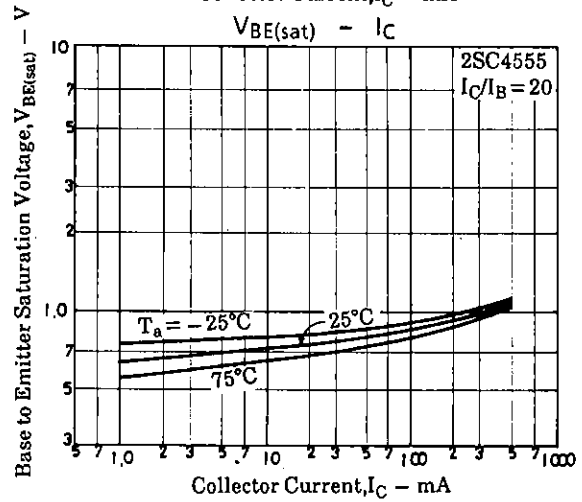
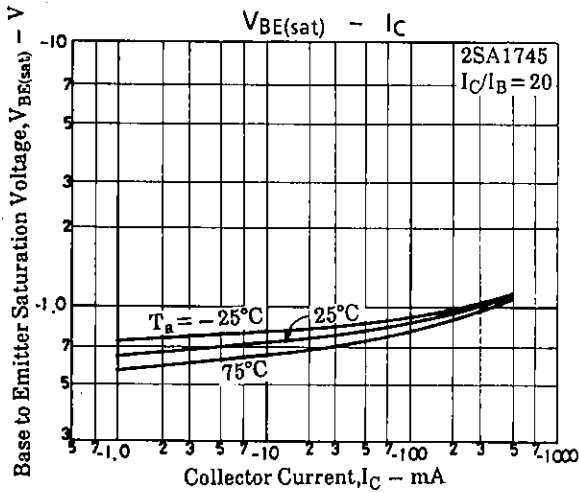
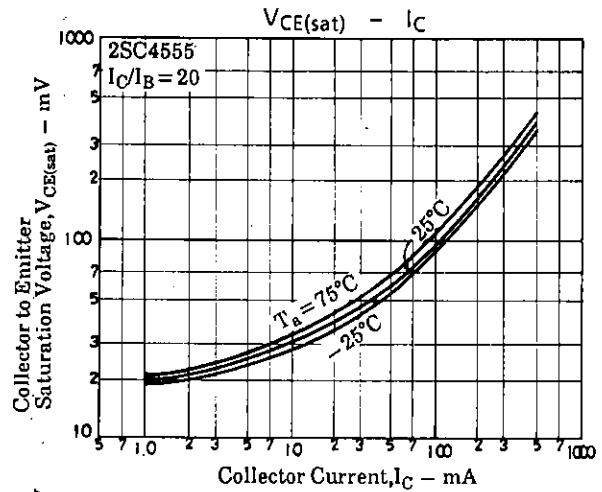
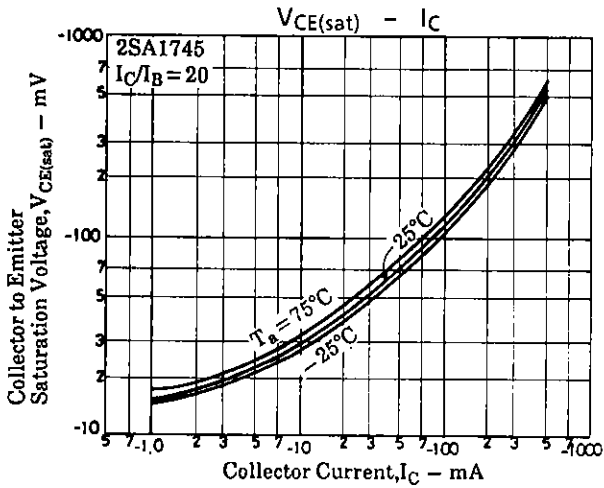
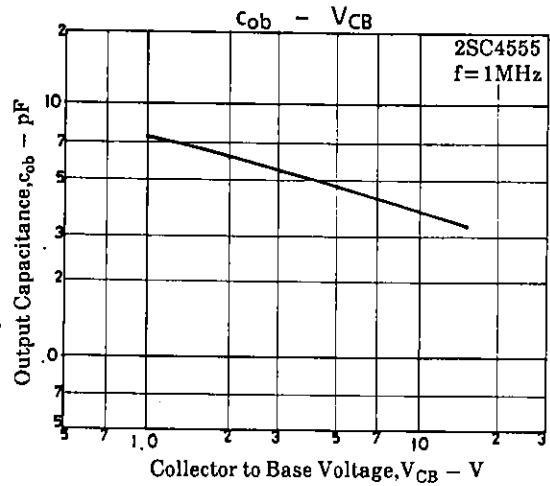
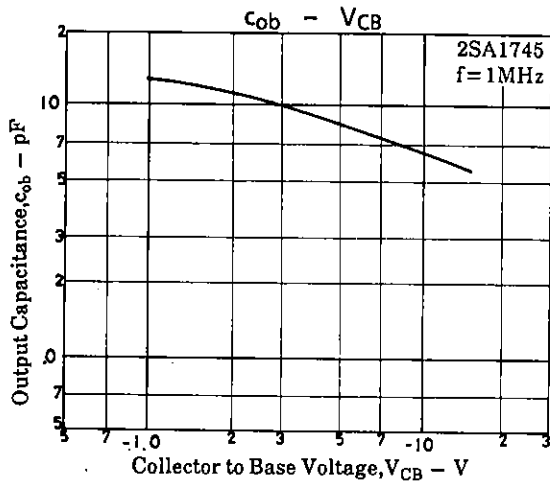
(unit : mm)

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2SA1745/2SC4555



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